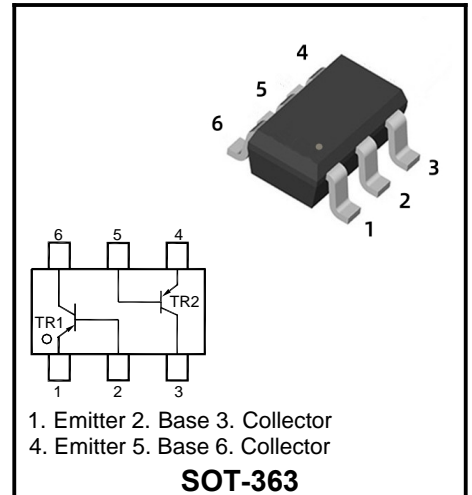


PNP Plastic-Encapsulate Transistors
DUAL TRANSISTOR
Features

- Epitaxial Planar Die Construction
- Ideal for Low Power Amplification and Switching

Marking Code

MMDT4403DW	K2T
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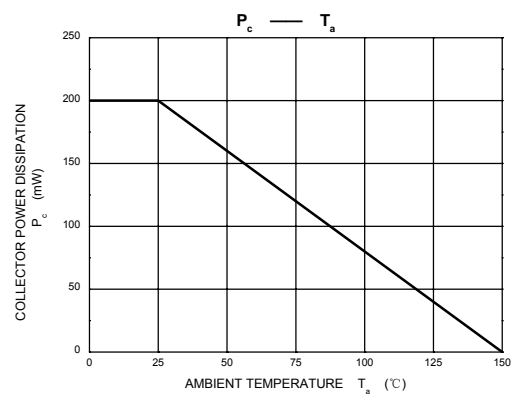
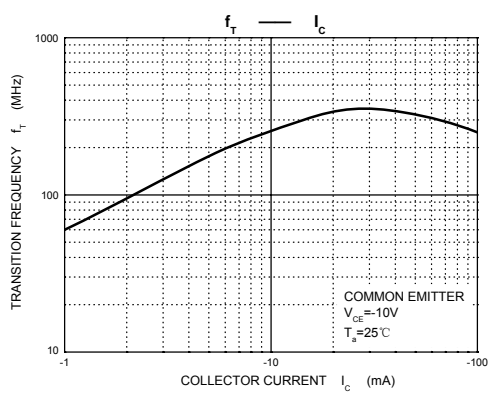
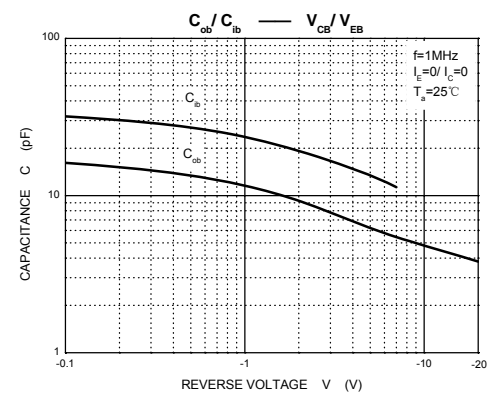
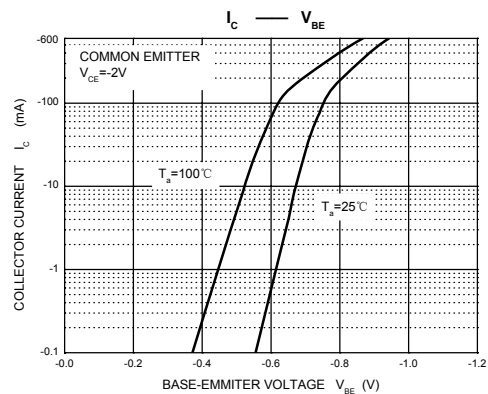
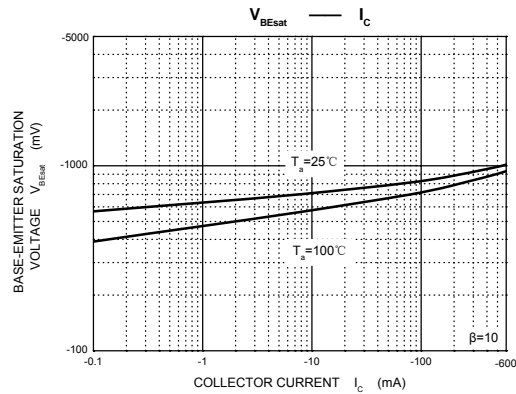
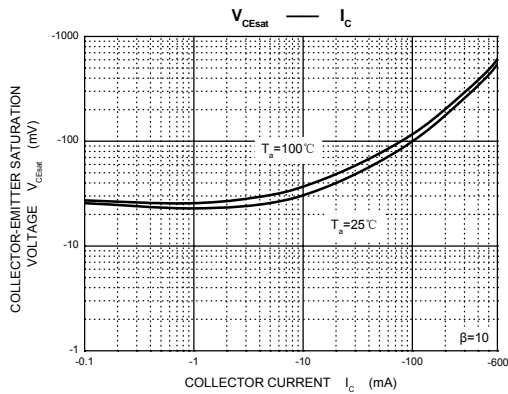
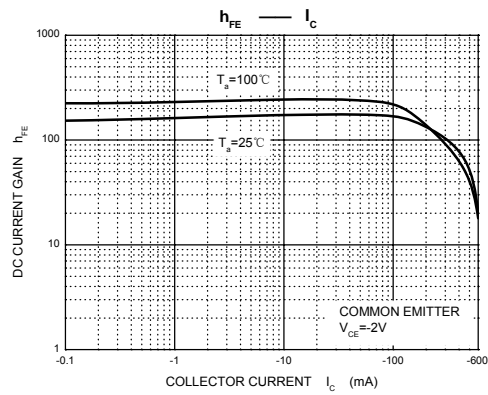
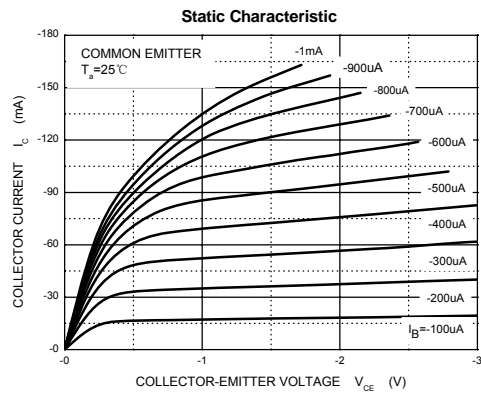

Maximum Ratings (Ta=25°C unless otherwise specified.)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-40	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-0.6	A
P_C	Collector Power Dissipation	0.2	W
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	625	°C/W
T_J	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55 to +150	°C

Electrical Characteristics (Ta=25°C unless otherwise specified.)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu A, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -50V, I_E = 0$			-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -35V, I_B = 0$			-0.5	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -1V, I_C = -0.1mA$	30			
	$h_{FE(2)}$	$V_{CE} = -1V, I_C = -1mA$	60			
	$h_{FE(3)}$	$V_{CE} = -1V, I_C = -10mA$	100			
	$h_{FE(4)}$	$V_{CE} = -2V, I_C = -150mA$	100		300	
	$h_{FE(5)}$	$V_{CE} = -2V, I_C = -500mA$	20			
Collector-emitter saturation voltage	$V_{CE(sat)1}$	$I_C = -150mA, I_B = -15mA$			-0.4	V
	$V_{CE(sat)2}$	$I_C = -500mA, I_B = -50mA$			-0.75	V
Base-emitter saturation voltage	$V_{BE(sat)1}$	$I_C = -150mA, I_B = -15mA$	-0.75		-0.95	V
	$V_{BE(sat)2}$	$I_C = -500mA, I_B = -50mA$			-1.3	V
Transition frequency	f_T	$V_{CE} = -10V, I_C = -20mA, f = 100MHz$	200			MHz
Output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$			8.5	pF
Delay time	t_d	$V_{CC} = -30V, V_{BE} = -2V, I_C = -150mA, I_{B1} = -15mA$			15	nS
Rise time	t_r				20	nS
Storage time	t_s	$V_{CC} = -30V, I_C = -150mA$			225	nS
Fall time	t_f	$I_{B1} = -I_{B2} = -15mA$			30	nS

Typical Characteristics



Ordering information

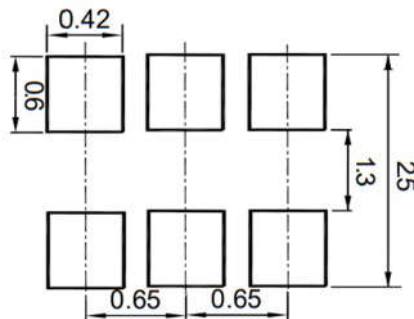
Package	Packing Description	Packing Quantity
SOT-363	Tape/Reel, 7" reel	3000PCS/Reel 120000PCS/Carton

Package Dimensions

SOT-363

Dim.	Millimeter(mm)		mil	
	Min.	Max.	Min.	Max.
A	0.8	1.1	32	43
A1	-	0.1	-	3.94
bp	0.20	0.30	7.87	11.81
c	0.10	0.25	3.94	9.84
D	1.8	2.2	70.87	86.61
E	1.15	1.35	45.28	53.15
e	1.3		51.18	
e1	0.65		25.6	
HE	2.0	2.2	78.74	86.6
Lp	0.15	0.45	5.90	17.71
Q	0.15	0.25	5.90	9.84
v	0.2		7.78	
w	0.2		7.78	
y	0.1		3.94	

The recommended mounting pad size



Disclaimer

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